

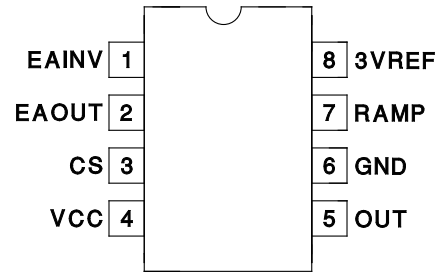
ABSOLUTE MAXIMUM RATINGS

VCC	35V
EAINV	–0.6V to VCC
IEAOUT	25mA
RAMP	–0.3V to 4V
CS	–0.3V to VCC
IOU	–0.7A to 0.7A
I3VREF	–15mA
Storage Temperature	–65°C to +150°C
Junction Temperature	–65°C to +150°C
Lead Temperature (Soldering, 10 sec.)	+300°C

*Currents are positive into, negative out of the specified terminal.
Consult Packaging Section of Databook for thermal limitations
and considerations of packages.*

CONNECTION DIAGRAMS

**DIL-8, SOIC-8 (TOP VIEW)
J or N, D Packages**



ELECTRICAL CHARACTERISTICS Unless otherwise stated, these parameters apply for $T_A = -55^\circ\text{C}$ to $+125^\circ\text{C}$ for the UC1572, -40°C to $+85^\circ\text{C}$ for the UC2572, and 0°C to $+70^\circ\text{C}$ for the UC3572, $V_{CC} = 5\text{V}$, $C_T = 680\text{pF}$, $T_A = T_J$.

PARAMETER	TEST CONDITION	MIN	TYP	MAX	UNITS
Reference Section					
3VREF		2.94	3	3.06	V
Line Regulation	$V_{CC} = 4.75$ to 30V		1	10	mV
Load Regulation	$I_{3VREF} = 0\text{V}$ to -5mA		1	10	mV
Oscillator Section					
Frequency	$V_{CC} = 5\text{V}$ to 30V	85	100	115	kHz
Error Amp Section					
EAINV	EAOUT = 2V	–10	0	10	mV
	$I_{EAINV} = -1\text{mA}$		–0.2	–0.9	V
IEAINV	EAOUT = 2V		–0.2	–1.0	μA
AVOL	EAOUT = 0.5V to 3V	65	90		dB
EAOUT High	EAINV = –100mV	3.6	4	4.4	V
EAOUT Low	EAINV = 100mV		0.1	0.2	V
IEAOUT	EAINV = –100mV, EAOUT = 2V	–350	–500		μA
	EAINV = 100mV, EAOUT = 2V	7	20		mA
Unity Gain Bandwidth	$T_J = 25^\circ\text{C}$, $F = 10\text{kHz}$	0.6	1		MHz
Current Sense Comparator Section					
Threshold		0.195	0.215	0.235	V
Input Bias Current	$CS = 0$		–0.4	–1	μA
CS Propagation Delay			300		ns
Gate Drive Output Section					
OUT High Saturation	$I_{OUT} = 0$		0	0.3	V
	$I_{OUT} = -10\text{mA}$		0.7	1.5	V
	$I_{OUT} = -100\text{mA}$		1.5	2.5	V
OUT Low Saturation	$I_{OUT} = 10\text{mA}$		0.1	0.4	V
	$I_{OUT} = 100\text{mA}$		1.5	2.2	V
Rise Time	$T_J = 25^\circ\text{C}$, $C_{LOAD} = 1\text{nF} + 3.3\text{ Ohms}$		30	80	ns
Fall Time	$T_J = 25^\circ\text{C}$, $C_{LOAD} = 1\text{nF} + 3.3\text{ Ohms}$		30	80	ns
Pulse Width Modulator Section					
Maximum Duty Cycle	EAINV = +100mV, $V_{CC} = 5\text{V}$ to 30V		92	96	%
Minimum Duty Cycle	EAINV = –100mV, $V_{CC} = 5\text{V}$ to 30V			0	%
Modulator Gain	EAOUT = 1.5V to 2.5V	45	55	65	%/V

ELECTRICAL CHARACTERISTICS (cont.) Unless otherwise stated, these parameters apply for $T_A = -55^{\circ}\text{C}$ to $+125^{\circ}\text{C}$ for the UC1572, -40°C to $+85^{\circ}\text{C}$ for the UC2572, and 0°C to $+70^{\circ}\text{C}$ for the UC3572, $V_{CC} = 5\text{V}$, $C_T = 680\text{pF}$, $T_A = T_J$.

PARAMETER	TEST CONDITION	MIN	TYP	MAX	UNITS
Undervoltage Lockout Section					
Start Threshold		3.5	4.2	4.7	V
Hysteresis		100	200	300	mV
Sleep Mode Section					
Threshold		1.8	2.2	2.6	V
Supply Current Section					
I _{vcc}	V _{CC} = 5V, 30V		9	12	mA
	V _{CC} = 30, C _S = 3V		50	150	μA

PIN DESCRIPTIONS

3VREF: Precision 3V reference. Bypass with 100nF capacitor to GND.

CS: Current limit sense pin. Connect to a ground referenced current sense resistor in series with the flyback inductor. OUT will be held high (PMOS switch off) if CS exceeds 0.2V.

EAINV: Inverting input to error amplifier. Summing junction for 3VREF and VOUT sense. The non-inverting input of the error amplifier is internally connected to GND.

EAOUT: Output of error amplifier. Use EAOUT and EAINV for loop compensation components.

GND: Circuit Ground.

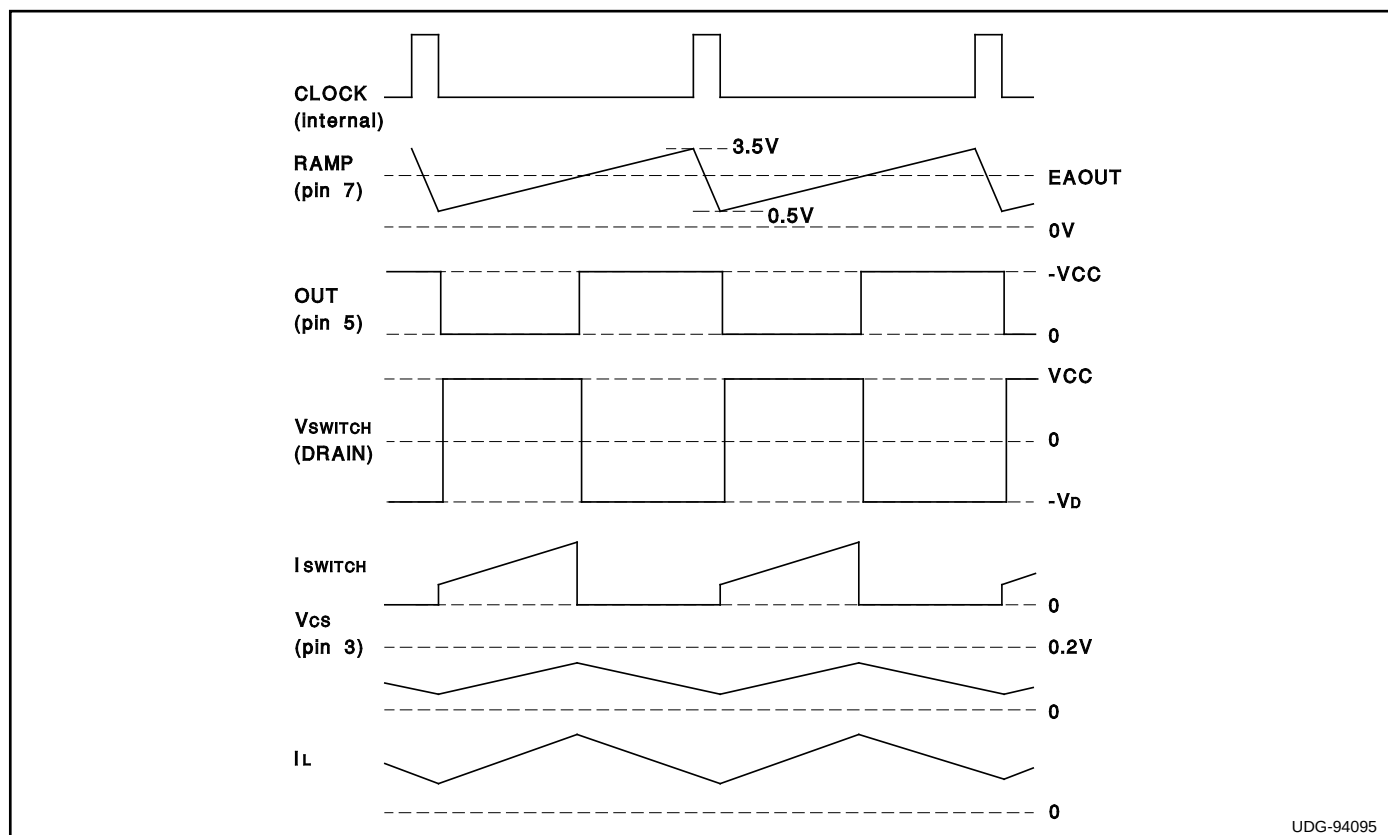
OUT: Gate drive for external PMOS switch connected between VCC and the flyback inductor. OUT drives the gate of the PMOS switch between VCC and GND.

RAMP: Oscillator and ramp for pulse width modulator. Frequency is set by a capacitor to GND by the equation

$$F = \frac{1}{15k \cdot C_{RAMP}}$$

Recommended operating frequency range is 10kHz to 200kHz.

VCC: Input voltage supply to chip. Range is 4.75 to 30V. Bypass with a 1μF capacitor.



UDG-94095

Typical Waveforms

TYPICAL APPLICATION : +5V TO -12V FLYBACK CONVERTER

